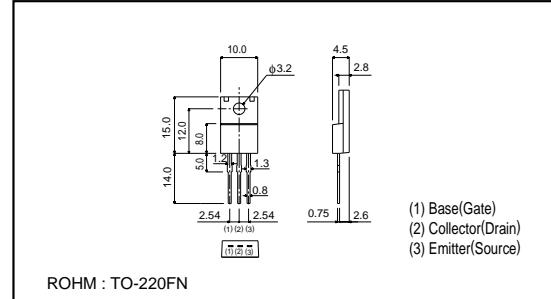


Transistors

High-speed Switching Transistor (-60V,-12A)**2SA2007****●Features**

- 1) High switching speed.
(Typ. $t_f = 0.15\mu s$ at $I_c = -6A$)
- 2) Low saturation voltage.
(Typ. $V_{CE(sat)} = -0.2V$ at $I_c / I_B = -6A / -0.3A$)
- 3) Wide SOA. (safe operating area)
- 4) Complements the 2SC5526.

●External dimensions (Units : mm)**●Absolute maximum ratings ($T_a = 25^\circ C$)**

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	-100	V
Collector-emitter voltage	V_{CEO}	-60	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_c	-12 -20	A A(Pulse)
Collectorpowerdissipation	P_c	2 25	W W($T_c = 25^\circ C$)
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ C$

●Packaging specifications and h_{FE}

Type	2SA2007
Package	TO-220FN
h_{FE}	F
Code	-
Basic ordering unit (pieces)	500

●Electrical characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-100	-	-	V	$I_c = -50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	-60	-	-	V	$I_c = -1mA$
Emitter-base breakdown voltage	BV_{EBO}	-5	-	-	V	$I_e = -50\mu A$
Collector cutoff current	I_{CBO}	-	-	-10	μA	$V_{CB} = -100V$
Emitter cutoff current	I_{EBO}	-	-	-10	μA	$V_{EB} = -5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	-0.3	V	$I_c/I_b = -6A/-0.3A$
		-	-	-0.5	V	$I_c/I_b = -8A/-0.4A$
Base-emitter saturation voltage	$V_{BE(sat)}$	-	-	-1.2	V	$I_c/I_b = -6A/-0.3A$
		-	-	-1.5	V	$I_c/I_b = -8A/-0.4A$
DC current transfer ratio	h_{FE}	160	-	320	-	$V_{CE} = -2V, I_c = -2A$
Transition frequency	f_T	-	80	-	MHz	$V_{CE} = -10V, I_c = 1A, f = 30MHz$
Output capacitance	C_{ob}	-	250	-	pF	$V_{CB} = -10V, I_c = 0A, f = 1MHz$
Turn-on time	t_{on}	-	-	0.3	μs	$I_c = -6A, R_L = 5\Omega$
Storage time	t_{stg}	-	-	1.5	μs	$I_{B1} = -I_{B2} = -0.3A$
Fall time	t_f	-	-	0.3	μs	$V_{CC} = -30V$